Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A plasma CVD apparatus comprising:

a vacuum chamber;

an exhaust means for exhausting the gas from the vacuum chamber to an outside;

an electrode for supplying an electric energy inside the vacuum chamber;

a supporting means for supporting a substrate opposing the electrode wherein said substrate is moved in a first direction through said chamber;

an introducing port for gas, ~~located~~ located between the electrode and the substrate wherein said gas is introduced into said chamber in a direction parallel with said first direction;

wherein a plurality of openings are located on a surface of the electrode opposing the substrate,

wherein the gas is exhausted from the plurality of openings to the outside of the vacuum chamber.

2. (Currently Amended) An apparatus according to claim 1, further comprising:

a transporting means for transporting continuously ~~a flexible~~ the substrate in said first direction.

3. (Original) An apparatus according to claim 1, wherein each of the plurality of openings is circular,

wherein the plurality of openings are located on the surface of the electrode at constant intervals.

4. (Original) An apparatus according to claim 1, wherein the electrode is a mesh-like plate.

5. (Cancelled)

6. (Previously presented) An apparatus according to claim 1 further comprising:

a second electrode opposing the first electrode for supplying the electric energy inside the vacuum chamber.

7. (Previously presented) An apparatus according to claim 6,

wherein the substrate is supported between the first and second electrodes by the supporting means.

8. (Previously presented) An apparatus according to claim 2,

wherein the transporting means includes at least one selected from the group consisting of an unwinding roll and a winding roll.

9. (currently amended) The apparatus according to claim 1 wherein said substrate is located horizontally and ~~said~~ has a substrate surface ~~downward~~ that is downwardly opposed to the electrode.

10. (Currently Amended) An apparatus comprising:

a chamber;

a first electrode in the chamber;

a second electrode in the chamber;

a substrate holder to hold a substrate between the first and second electrode wherein said substrate is moved in a first direction through said chamber;

at least one gas inlet port to introduce a gas to a space between the substrate and the second electrode wherein said gas is introduced in a direction parallel to said first direction; and

a plurality of gas exhaust ports provided in said second electrode through which said gas is exhausted from said space.

11. (Previously presented) The apparatus according to claim 10 wherein said first electrode is grounded.

12. (Previously presented) The apparatus according to claim 10 wherein said second electrode is located below said first electrode.

13. (Previously presented) The apparatus according to claim 10 wherein said apparatus is a film formation apparatus.

14. (Previously presented) The apparatus according to claim 10 wherein said gas inlet port is located in a position between the substrate and the second electrode.

15. (Withdrawn) A method comprising:

providing a first electrode and a second electrode opposed to said first electrode in a chamber wherein said second electrode is provided with a plurality of openings;

disposing a substrate between said first electrode and said second electrode;

introducing a gas into said chamber through a gas introducing port;

applying an electrical energy between the first and second electrodes to produce a plasma of said gas; and

exhausting said gas from said chamber through said plurality of openings of the second electrode.

16. (Withdrawn) The method according to claim 15 further comprising a step of moving said substrate with respect to said first and second electrodes during the application of said electrical energy.

17. (Withdrawn) The method according to claim 15 wherein said second electrode is located below said first electrode.

18. (Withdrawn) The method according to claim 15 wherein said gas introducing port is located in a position between the substrate and the second electrode.

19. (Withdrawn) The method according to claim 15 further comprising a step of forming a film on said substrate by plasma CVD from said plasma.

20. (New) The plasma CVD apparatus according to claim 1 further comprising an abnormal discharge preventing plate between said exhaust means and said electrode wherein said abnormal discharge preventing plate has a plurality of openings.

21. (New) The plasma CVD apparatus according to claim 10 further comprising an abnormal discharge preventing plate between said second electrode and exhausting port of the chamber wherein said abnormal discharge preventing plate has a plurality of openings.